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10EE764

Seventh Semester B.E. Degree Examination, Jan./Feb. 2021

VLSI Circuits and Design

Time: 3 hrs.

Max. Marks:100

Note: 1. Answer any FIVE full questions, selecting at least TWO questions from each part.
2. Missing data suitably assumed.

PART - A

- 1 a. Explain Moore's law with graph. (04 Marks)
b. Explain in detail the n-well process of fabrication. Draw the cross sectional view of n-well CMOS inverter. (10 Marks)
c. Write a note on production of E-beam masks. (06 Marks)
- 2 a. Explain drain-to-source current voltage relationships for non-saturated and saturated regions. (10 Marks)
b. Explain the transfer characteristic in β ratio for a CMOS inverter. (10 Marks)
- 3 a. With relevant diagrams, explain the Lambda based design rules as applicable to p-well CMOS process. (10 Marks)
b. Explain in brief the MOS layers. Draw the stick diagram and layout for an NMOS two way selector, with enable input. (10 Marks)
- 4 a. Discuss the time constants in VLSI circuits, with an example of inverter delay. (10 Marks)
b. What is area capacitance and standard unit of capacitance? Calculate the total area capacitance for the multilayered structure shown in Fig.Q4(b). Assume for $5 \mu\text{m}$ technology. Also calculate the C_{in} and C_{out} values of the capacitances for the given structure:
 - (i) Metal 1 to substrate: $0.075 \times 10^{-4} \text{ pF}/\mu\text{m}^2$
 - (ii) Polysilicon to substrate : $0.1 \times 10^{-4} \text{ pF}/\mu\text{m}^2$
 - (iii) Gate to channel : $1 \times 10^{-4} \text{ pF}/\mu\text{m}^2$

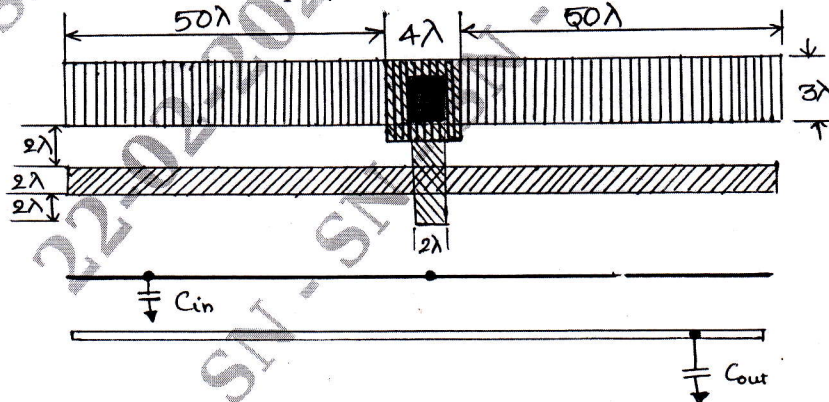


Fig.Q4(b)

(10 Marks)

PART - B

- 5 a. What are different scaling models? Indicate the scaling factors for the device parameters. (10 Marks)
b. Discuss limitation of scaling for logic levels and supply voltage due to noise. (10 Marks)

- 6 a. Explain in detail: (i) Pseudo nMOS logic (ii) Dynamic CMOS logic (10 Marks)
b. Explain the structured design of bus arbitration logic for n lines. Also, write the circuit diagram and the stick diagram for a single cell. (10 Marks)
- 7 a. Explain the general arrangement of a 4-bit arithmetic processor. (10 Marks)
b. Explain the operation of 4×4 cross bar switch with a neat diagram. (10 Marks)
- 8 a. Define regularity. Explain some observations on the design process. (10 Marks)
b. With a neat diagram and relevant expressions, explain the implementation of a 4 bit ALU, using full adders. (10 Marks)
